REMARKS

Claims 1-45 are pending in this application, with claims 1, 5, 9, 13, 17 and 21 being independent. Claims 1, 5, 9, 13, 17, and 21 have been amended herein by virtue of this amendment. No new matter has been introduced.

Claims 1, 5, 9, 13, 17, and 21 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The amendments to these claims, by which the particular features of these claims that were identified as lacking written description have been deleted, are believed to address this rejection. Accordingly, Applicant requests that the rejection be withdrawn. Applicant, however, does not stipulate that these features lack written description under 35 U.S.C. 112, first paragraph, and reserves the right to pursue these claim features in this or continuing applications.

Claims 1-3, 5-7, 9-23, and 25-45 (Applicant notes that the listing of claims "9-23 and 25-45" appears to mistakenly be designated as claims "9-24" in the first line of paragraph 4 of the Office Action, and respectfully requests clarification on this issue) are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 6,040,819 to Someya (Someya) in view of U.S. Patent No. 6,229,508 to Kane (Kane) and U.S. Patent No. 6,518,977 to Naka et al. (Naka). Claims 4, 8, and 24 are rejected under 35 U.S.C. 103(a) as being unpatentable over Someya, Kane, and Naka, and further in view of U.S. Patent No. 4,070,663 to Kanatani et al. (Kanatani).

With respect to the rejection of claims 1-3, 5-7, 9-23, and 25-45, Applicant respectfully submits that none of Someya, Kane, or Naka, whether taken alone or in combination, disclose or properly suggest all of the limitations of at least independent claims 1, 5, 9, 13, 17, and 21, as amended.

For example, independent claim 1 recites:

> ...after each of the n+m display period begins completing the
> respective display period by turning on the third TFT...
> wherein the first TFT comprises a crystalline semiconductor film,
> a gate insulating film over the crystalline semiconductor film, first and
> second gate electrodes formed over the crystalline semiconductor film
> with the gate insulating film interposed therebetween, and first and second
> channel forming regions in the crystalline semiconductor film below the

first and second gate electrodes, respectively, and a pair of first impurity regions in the crystalline semiconductor film between the first and second channel forming regions and a third impurity region between the pair of first impurity regions.

Applicant respectfully submits that the above-recited claim language is supported at, for example, FIGS. 13A – 16 of Applicant's specification. The same or similar features are recited in independent claims 5, 9, 13, 17, and 21.
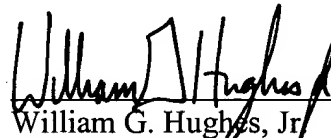
As none of the prior art of record, whether taken alone or in combination, discloses or properly suggests at least the above-referenced features, Applicant respectfully submits that independent claims 1, 5, 9, 13, 17, and 21 are allowable for at least these reasons. Therefore, Applicant submits that dependent claims 2-4, 6-8, 10-12, 14-16, 18-20, and 22-45 are allowable for at least the same reasons.

Based on the above, all of the claims are believed to be in condition for allowance, and, accordingly, such action is requested in the Examiner's next official communication.

Enclosed is a $1220 check (RCE filing fee $790 and Two-Month Extension of Time fee $430). Please apply any other charges or credits to deposit account 06-1050.

Respectfully submitted,

Date:___October 15, 2004_____

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